

Figure 1 consists of four cross-sectional views (a, b, c, d) of a semiconductor device, showing the progression of a manufacturing process. The device is built on a substrate 200, which has a layer 201 and a layer 202. A series of openings are formed in layer 202, and a material 203a is deposited in these openings. In view (a), a layer 204a is deposited over the entire surface, and a layer 206 is deposited in the openings. In view (b), a layer 214a is deposited over the entire surface, and a layer 206a is deposited in the openings. In view (c), a layer 215 is deposited over the entire surface, and a layer 206a is deposited in the openings. In view (d), a layer 214b is deposited over the entire surface, and a layer 206a is deposited in the openings. The layers 204a, 206a, 214a, and 214b are shown with different hatching patterns to indicate they are different materials or layers.